

Product Summary

BV _{DSS}	R _{DS(ON)} MAX	I _D MAX T _A = +25°C
20V	9.5mΩ @ V _{GS} = 4.5V	11.7A
	11mΩ @ V _{GS} = 2.5V	10.8A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

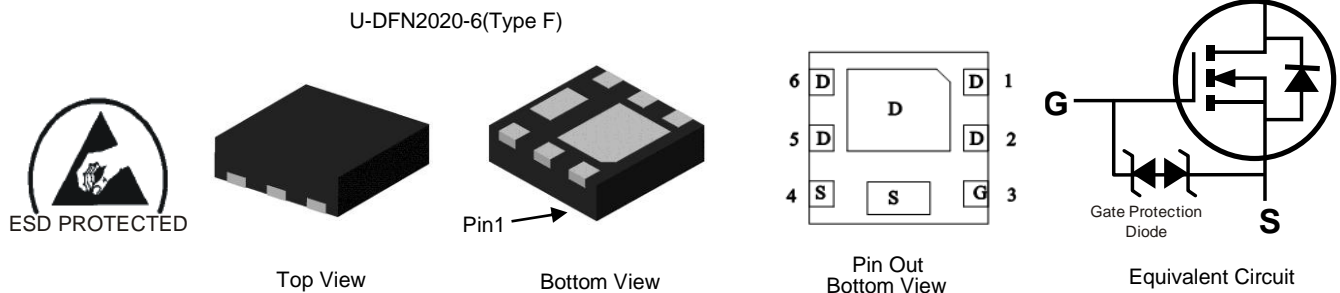
- General Purpose Interfacing Switch
- Power Management Functions

Features

- 0.6mm Profile – Ideal for Low Profile Applications
- PCB Footprint of 4mm²
- Low Gate Threshold Voltage
- Low On-Resistance
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact@diodes.com) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>**

Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 ^(e4)
- Weight: 0.0065 grams (Approximate)



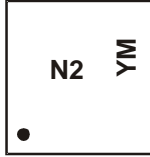
Ordering Information (Note 4)

Part Number	Case	Reel Size (inches)	Quantity per Reel
DMN2011UFDF-7	U-DFN2020-6 (Type F)	7	3,000
DMN2011UFDF-13	U-DFN2020-6 (Type F)	13	10,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information

Site 1



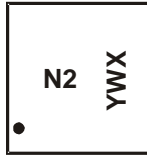
N2 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: H = 2020)
 M = Month (ex: 9 = September)

Date Code Key

Year	2016	...	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	D	...	H	I	J	K	L	M	N	O	P	R

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Site 2



D5 = Product Type Marking Code
 YWX = Date Code Marking
 Y = Year (ex: 0 = 2020)
 W = Week (ex: a = week 27; z represents week 52 and 53)
 X = Internal Code (ex: U = Monday)

Date Code Key

Year	2016	...	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	6	...	0	1	2	3	4	5	6	7	8	9

Week	1-26	27-52	53
Code	A-Z	a-z	z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	T	U	V	W	X	Y	Z

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V_{GSS}	± 12	V
Continuous Drain Current (Note 6) $V_{GS} = 4.5\text{V}$	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	11.7 9.3	A
	$t < 10\text{s}$	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	14.2 11.4	A
Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%)			I_{DM}	80	A
Maximum Body Diode Continuous Current			I_S	2.5	A
Avalanche Current (Notes 7) $L = 0.1\text{mH}$			I_{AS}	18	A
Avalanche Energy (Notes 7) $L = 0.1\text{mH}$			E_{AS}	17	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^\circ\text{C}$	P_D	0.73	W
	$T_A = +70^\circ\text{C}$		0.47	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	175	$^\circ\text{C/W}$
	$t < 10\text{s}$		128	
Total Power Dissipation (Note 6)	$T_A = +25^\circ\text{C}$	P_D	2.1	W
	$T_A = +70^\circ\text{C}$		1.3	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	61	$^\circ\text{C/W}$
	$t < 10\text{s}$		45	
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	9.3	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	20	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current $T_J = +25^\circ\text{C}$	I_{DSS}	—	—	1	μA	$V_{DS} = 16\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 10\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.4	—	1.0	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	6.5	9.5	m Ω	$V_{GS} = 4.5\text{V}, I_D = 7\text{A}$
			7.5	11		$V_{GS} = 2.5\text{V}, I_D = 7\text{A}$
			10	20		$V_{GS} = 1.8\text{V}, I_D = 5\text{A}$
			15	35		$V_{GS} = 1.5\text{V}, I_D = 3\text{A}$
Diode Forward Voltage	V_{SD}	—	0.7	1.2	V	$V_{GS} = 0\text{V}, I_S = 8.5\text{A}$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	2248	—	pF	$V_{DS} = 10\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	295	—	pF	
Reverse Transfer Capacitance 4	C_{rss}	—	265	—	pF	
Gate Resistance	R_g	—	1.5	—	Ω	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Total Gate Charge ($V_{GS} = 4.5\text{V}$)	Q_g	—	24	—	nC	$V_{DS} = 10\text{V}, I_D = 8.5\text{A}$
Total Gate Charge ($V_{GS} = 10\text{V}$)	Q_g	—	56	—	nC	
Gate-Source Charge	Q_{gs}	—	3.5	—	nC	
Gate-Drain Charge	Q_{gd}	—	5.1	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	3.6	—	ns	$V_{DS} = 10\text{V}, I_D = 8.5\text{A}$ $V_{GS} = 4.5\text{V}, R_g = 1.8\Omega$
Turn-On Rise Time	t_R	—	2.6	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	21.6	—	ns	
Turn-Off Fall Time	t_F	—	13.5	—	ns	
Reverse Recovery Time	T_{RR}	—	12.8	—	ns	
Reverse Recovery Charge	Q_{RR}	—	6.9	—	nC	$I_F = 8.5\text{A}, di/dt = 210\text{A}/\mu\text{s}$

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^\circ\text{C}$.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

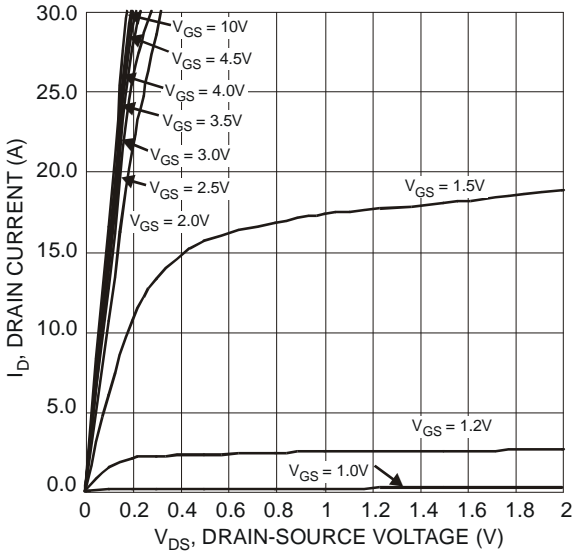


Figure 1 Typical Output Characteristic

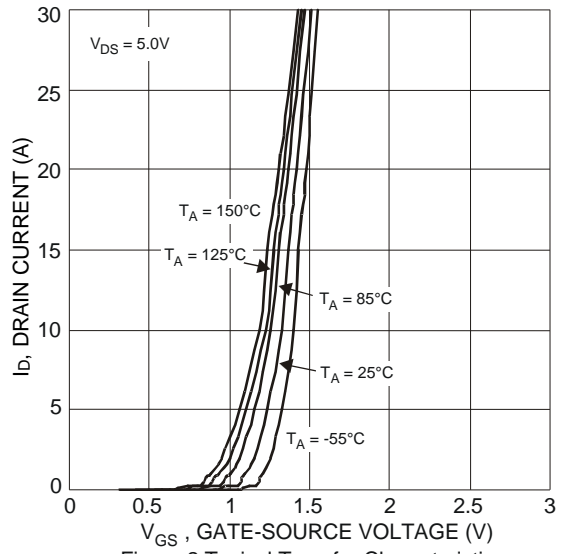


Figure 2 Typical Transfer Characteristics

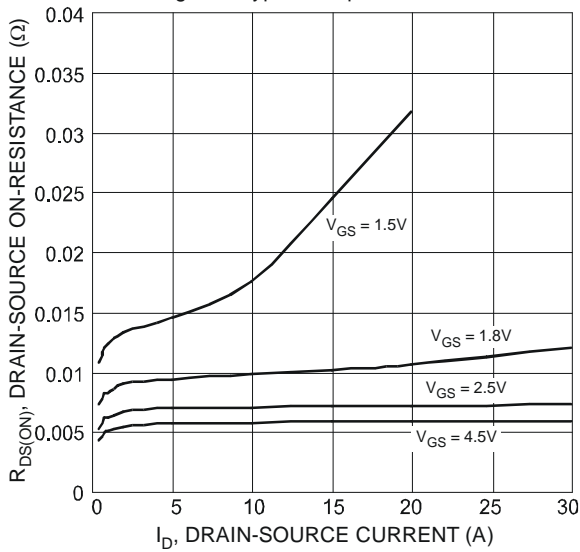


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

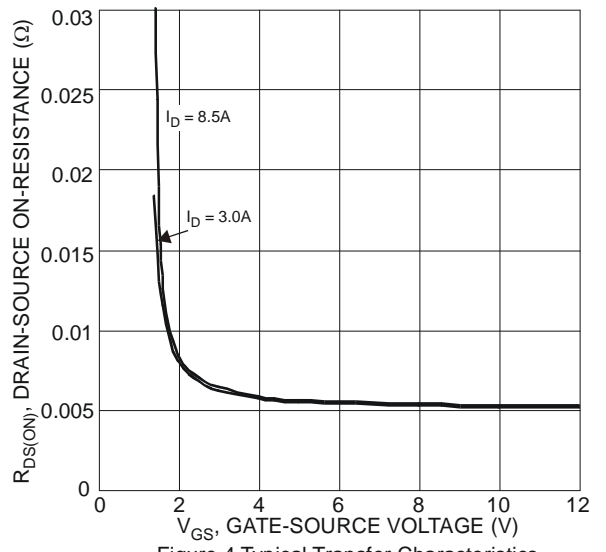


Figure 4 Typical Transfer Characteristics

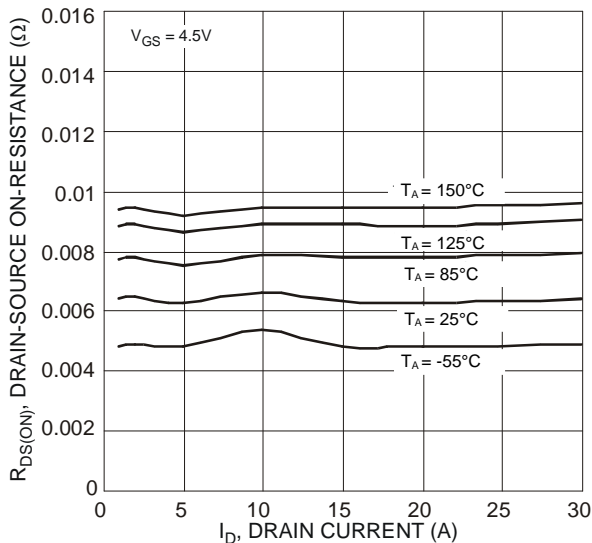


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

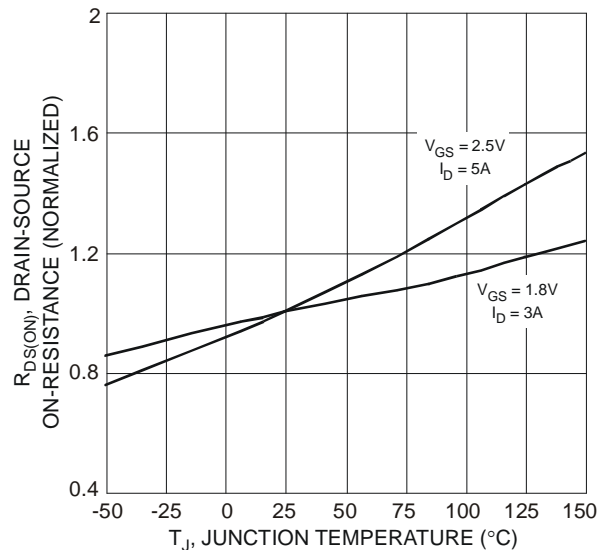


Figure 6 On-Resistance Variation with Temperature

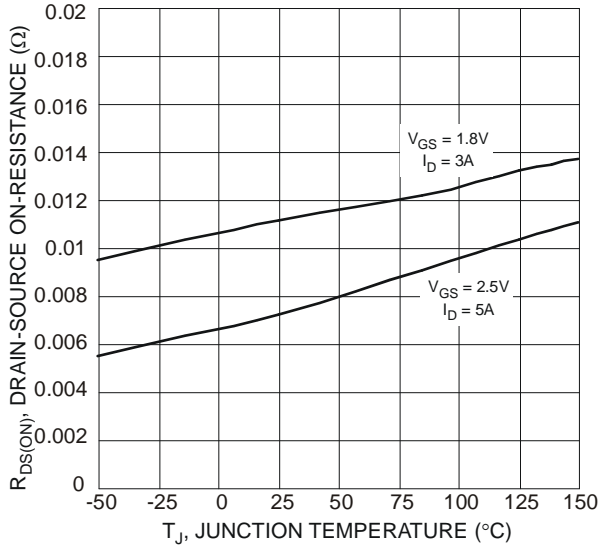


Figure 7 On-Resistance Variation with Temperature

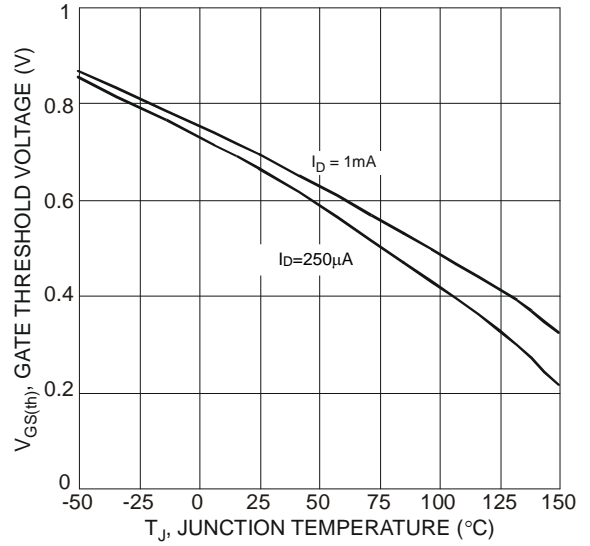


Figure 8 Gate Threshold Variation vs. Junction Temperature

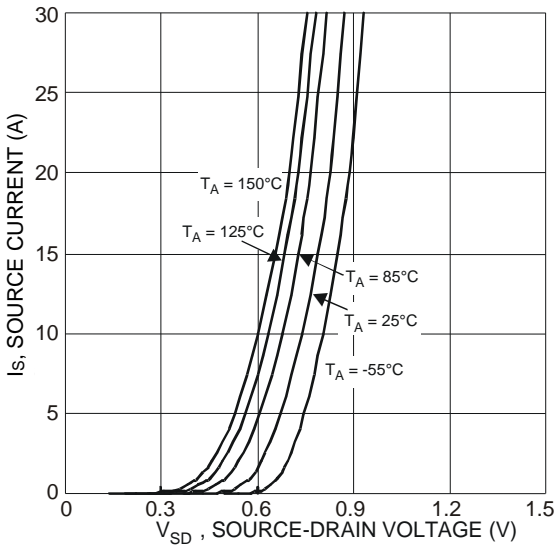


Figure 9 Diode Forward Voltage vs. Current

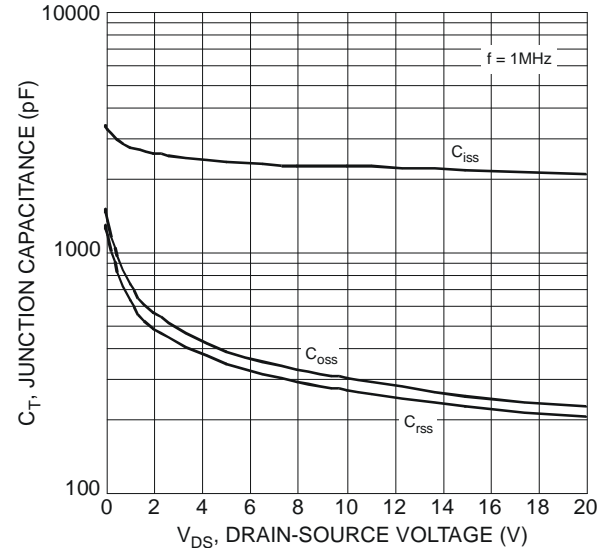


Figure 10 Typical Junction Capacitance

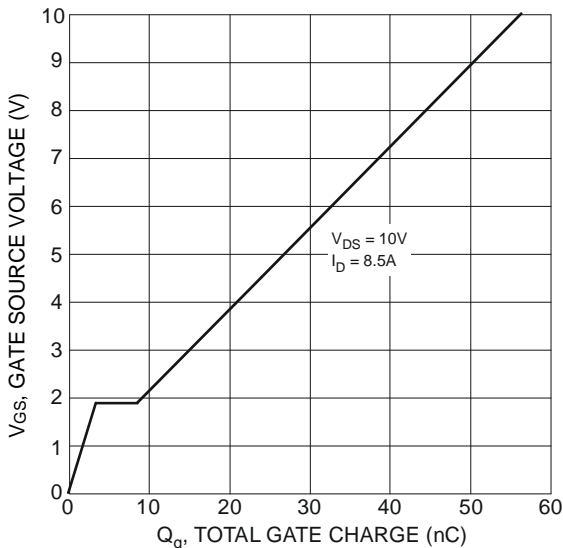


Figure 11 Gate Charge

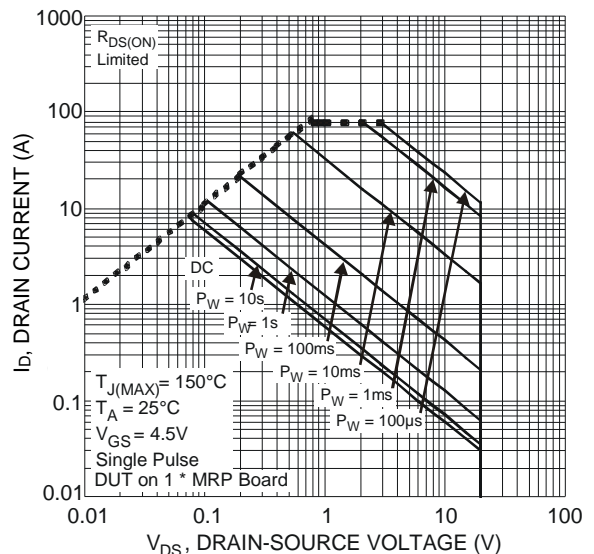
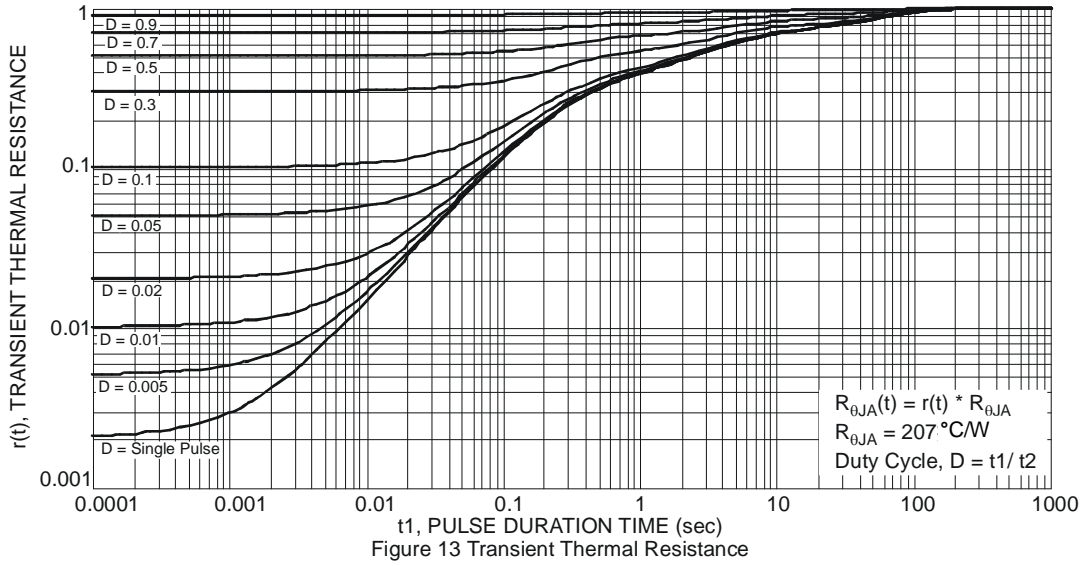


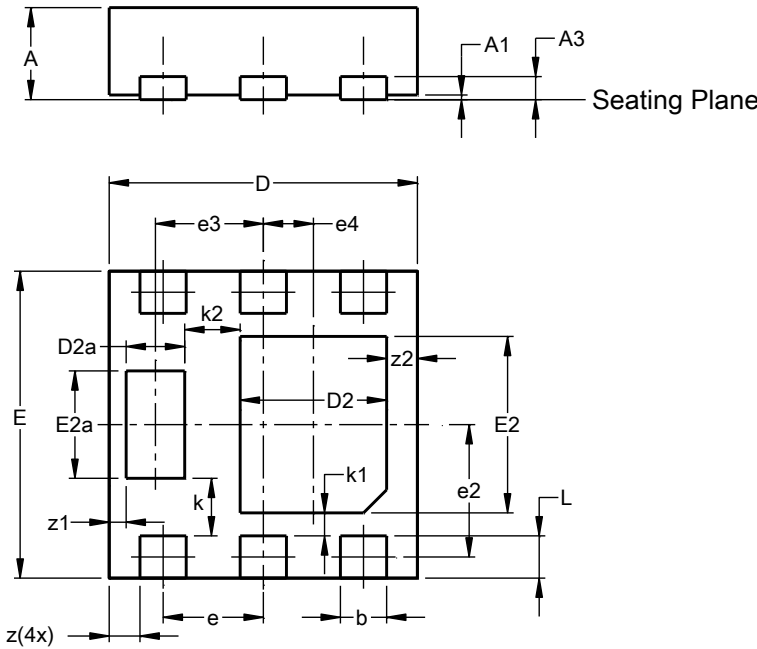
Figure 12 SOA, Safe Operation Area



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type F)

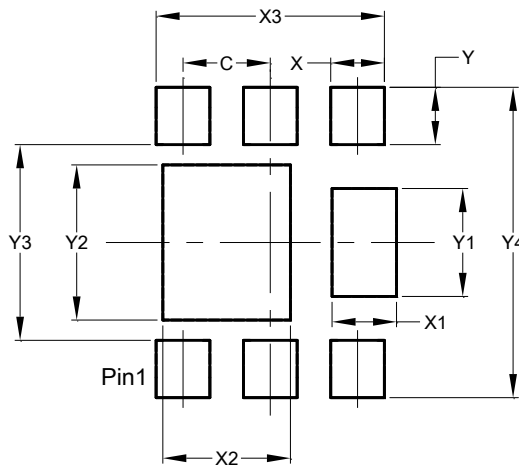


U-DFN2020-6 (Type F)			
Dim	Min	Max	Typ
A	0.57	0.63	0.60
A1	0.00	0.05	0.03
A3	-	-	0.15
b	0.25	0.35	0.30
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
D2a	0.33	0.43	0.38
E	1.95	2.05	2.00
E2	1.05	1.25	1.15
E2a	0.65	0.75	0.70
e	0.65 BSC		
e2	0.863 BSC		
e3	0.70 BSC		
e4	0.325 BSC		
k	0.37 BSC		
k1	0.15 BSC		
k2	0.36 BSC		
L	0.225	0.325	0.275
z	0.20 BSC		
z1	0.110 BSC		
z2	0.20 BSC		
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type F)



Dimensions	Value (in mm)
C	0.650
X	0.400
X1	0.480
X2	0.950
X3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300

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